

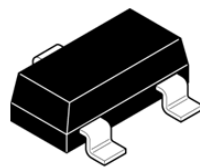
SOT23 PNP SILICON POWER (SWITCHING) TRANSISTOR

Features

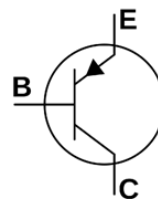
- 625mW POWER DISSIPATION
- I_C CONT = 2.5A
- I_C Up to 10A Peak Pulse Current
- Excellent h_{FE} Characteristics Up To 10A (pulsed)
- Low Saturation Voltage E.g. 10mV Typ.
- Low equivalent on-resistance $R_{CE(sat)}=97m\Omega$ at 1.5A
- Complementary part number FMMT618

Mechanical Data

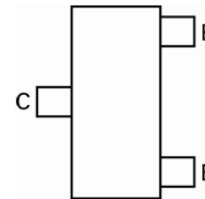
- Case: SOT-23
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (approximate)



Top View



Device symbol

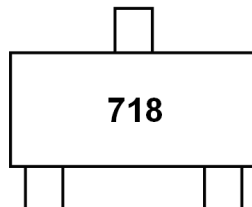


Pin Configuration

Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT718TA	718	7	8	3000
FMMT718TC	718	13	8	10000

Marking Information



718 = Product type Marking Code

FMMT718

SOT23 PNP SILICON POWER (SWITCHING) TRANSISTOR

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-1.5	A
Peak Pulse Current (Note 1)	I_{CM}	-6	A
Base Current	I_B	-500	mA

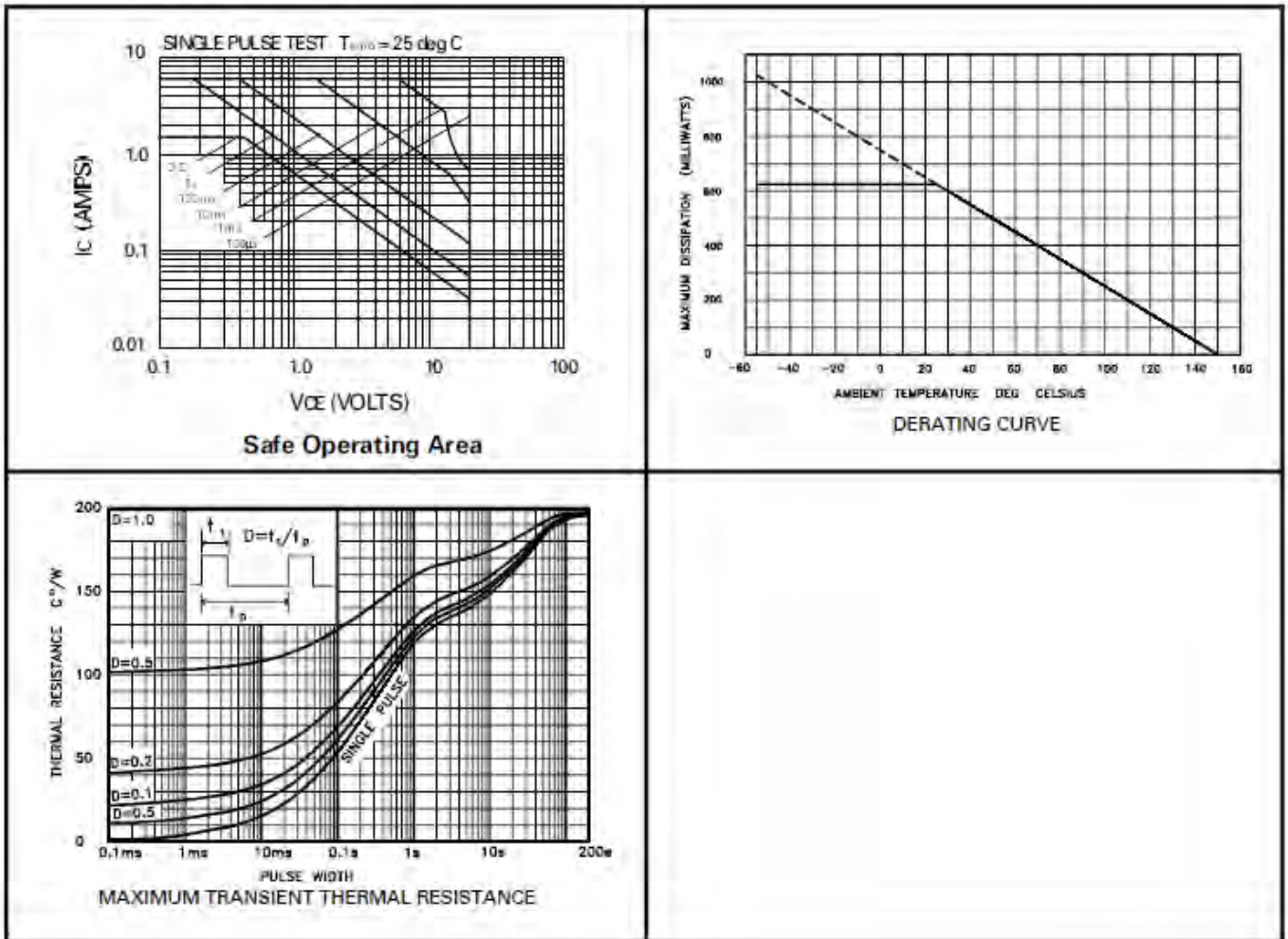
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = 25^\circ\text{C}$ (Note 2)	P_{tot}	625	mW
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Measured under pulse conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$
 2. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions

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Thermal Characteristics and Derating information



Note: Reference above figures, Devices were mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions

SOT23 PNP SILICON POWER (SWITCHING) TRANSISTOR

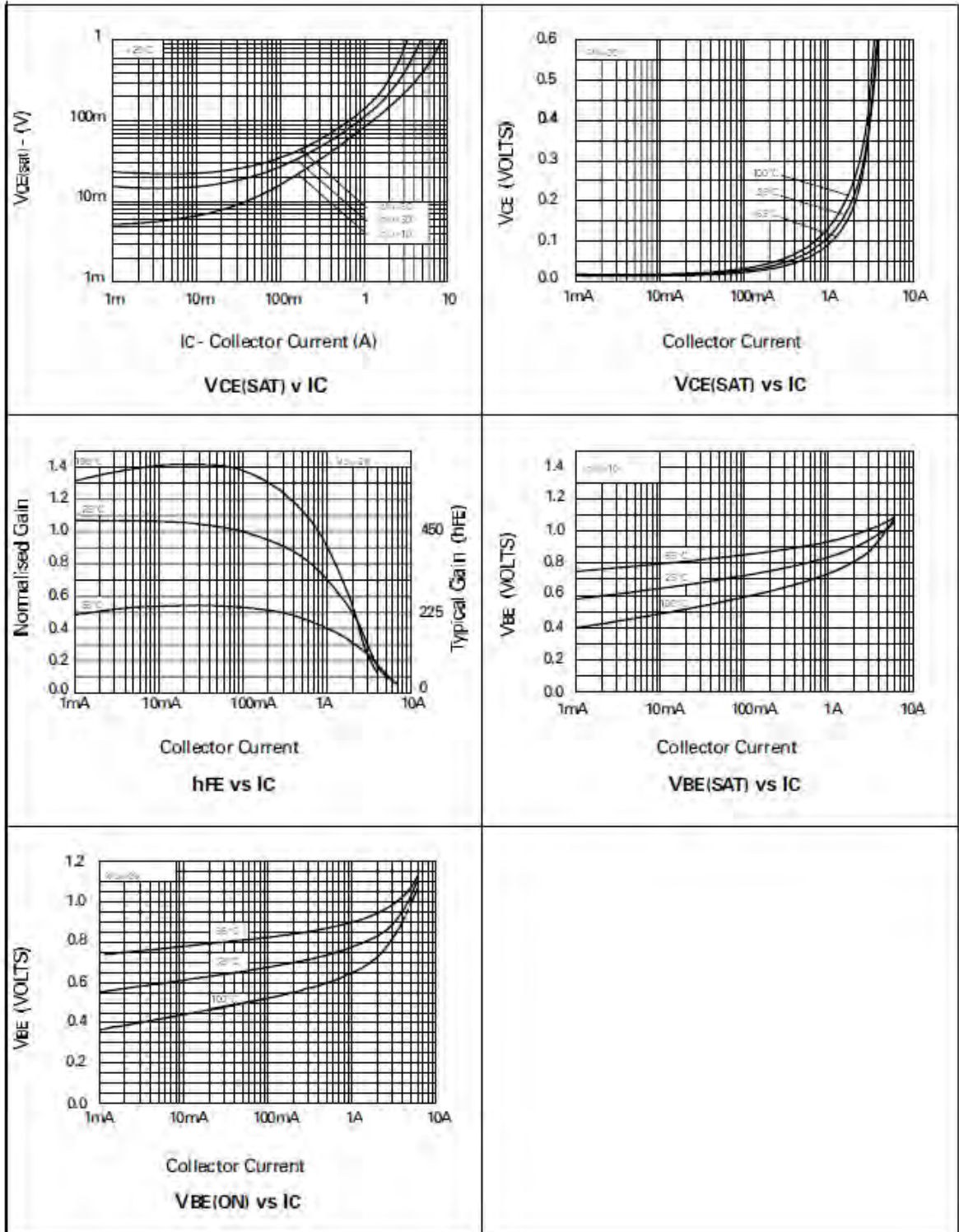
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	-65		V	I _C = -100 μA
Collector-Emitter Breakdown Voltage (Note 3)	V _{(BR)CEO}	-20	-55		V	I _C = -10 mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	-8.8		V	I _E = -100 μA
Collector Cutoff Current	I _{CBO}			-100	nA	V _{CB} = -15V
Emitter Cutoff Current	I _{EBO}			-100	nA	V _{EB} = -4V
Collector Emitter Cutoff Current	I _{CES}			-100	nA	V _{CE} = -15V
Static Forward Current Transfer Ratio (Note 3)	h _{FE}	300 300 150 35 15	475 450 230 70 30			I _C = -10mA, V _{CE} = -2V I _C = -100mA, V _{CE} = -2V I _C = -2A, V _{CE} = -2V I _C = -4A, V _{CE} = -2V I _C = -6A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 3)	V _{CE(sat)}		-16 -130 -145	-40 -200 -220	mV mV mV	I _C = -0.1A, I _B = -10mA I _C = -1A, I _B = -20mA I _C = -1.5A, I _B = -50mA
Base-Emitter Turn-On Voltage(Note 3)	V _{BE(on)}		-0.81	-1.0	V	I _C = -2A, V _{CE} = -2V
Base-Emitter Saturation Voltage(Note 3)	V _{BE(sat)}		-0.87	-1.0	V	I _C = -1.5A, I _B = -50mA
Output Capacitance	C _{obo}		21	30	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	150	180		MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-On Time	t _{on}		40		ns	V _{CC} = -10V, I _C = -1A
Turn-Off Time	t _{off}		670		ns	I _{B1} = I _{B2} = -20mA

Notes: 3. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%

SOT23 PNP SILICON POWER (SWITCHING) TRANSISTOR

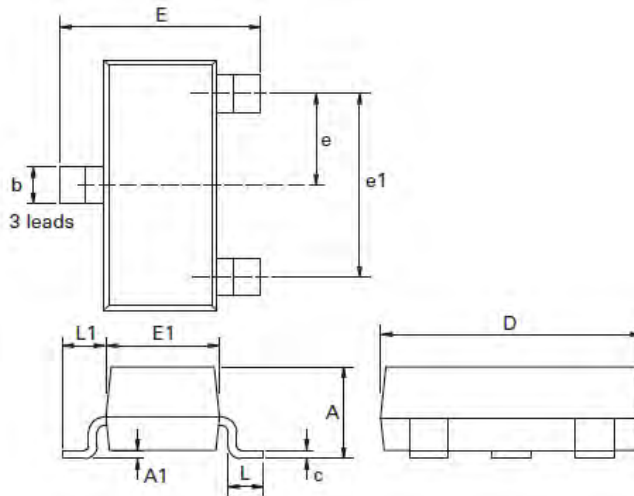
Typical Characteristics



FMMT718

SOT23 PNP SILICON POWER (SWITCHING) TRANSISTOR

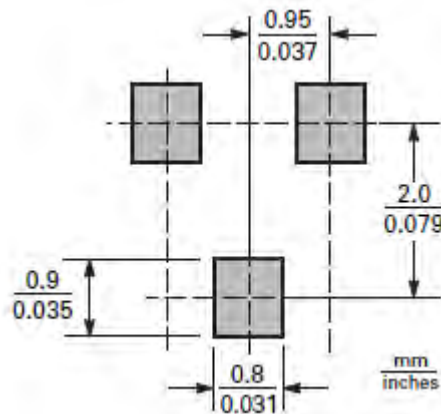
Package Outline Dimensions



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Suggested Pad Layout



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